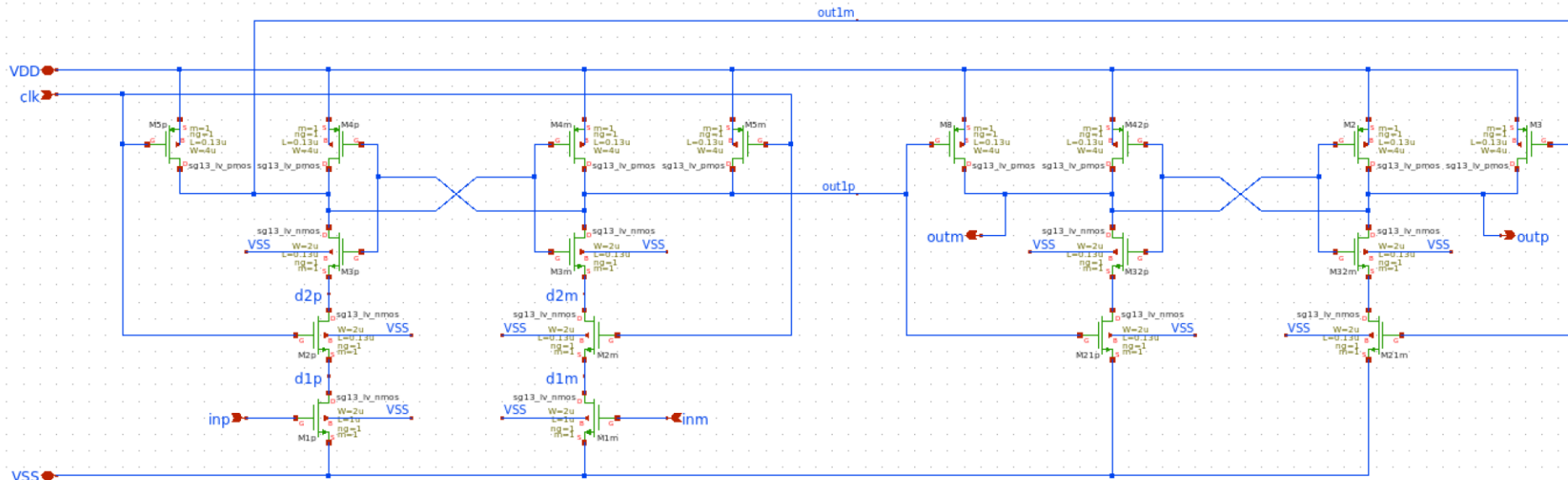


Inverter-Based Integrator

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Comparator with Storage Latch



Boris Murmann

x1. /foss/designs/comp.sch

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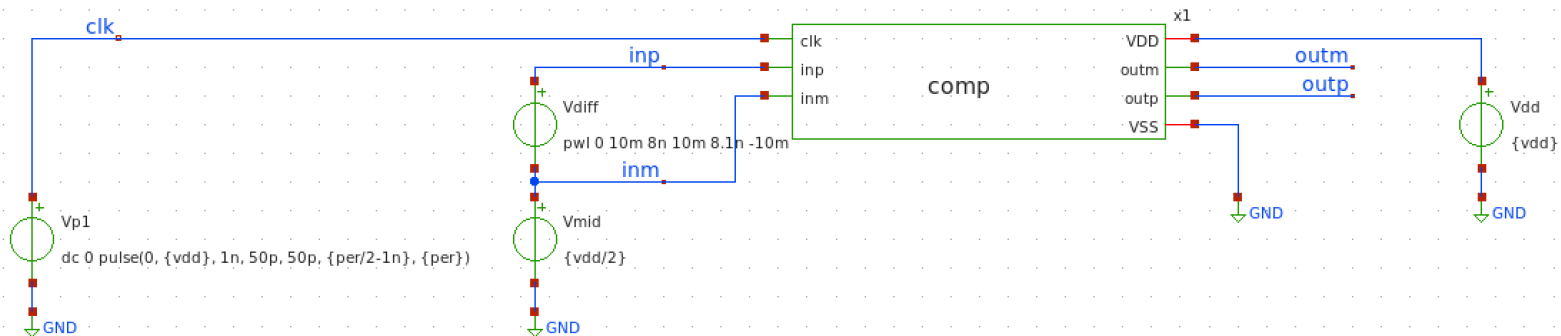
NGSPICE

```
.param temp=27 vdd=1.2 per=10n vdiff=10m
.option method=gear reltol=1e-5
.ic v(outp)=0

.control
save all
tran 10p 20n
plot clk x1.out1m x1.out1p
plot outm outp
.endc
```

MODEL

```
.lib $::SG13G2_MODELS/cornerMOSlv.lib mos_tt
```

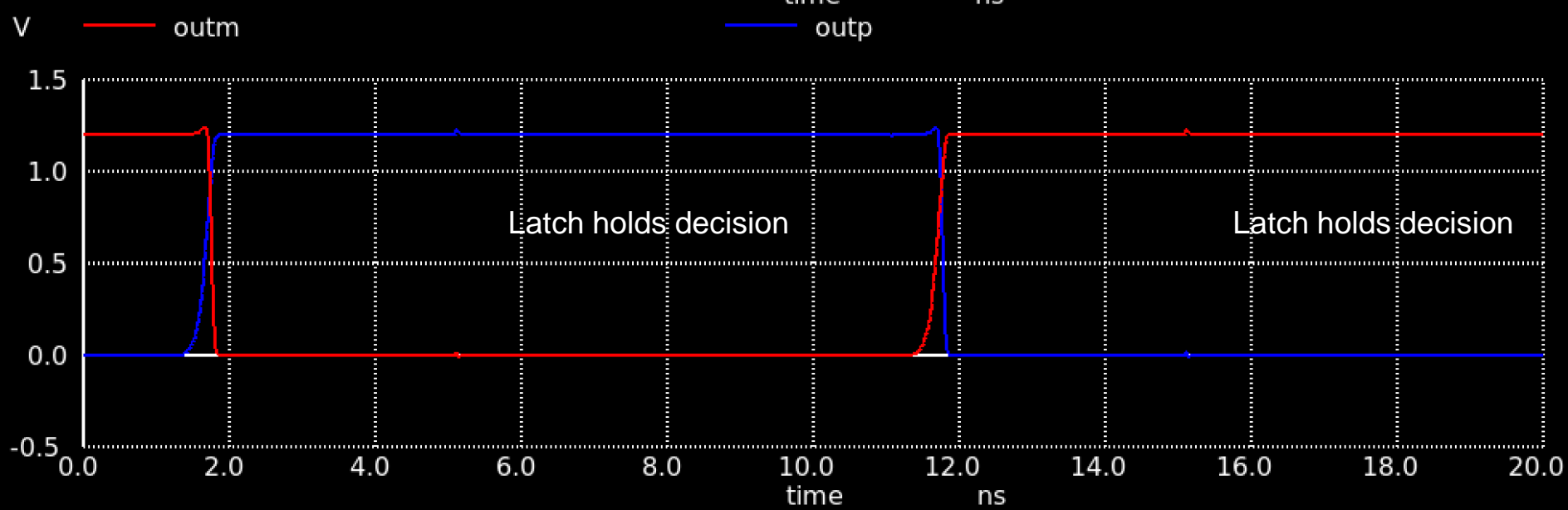
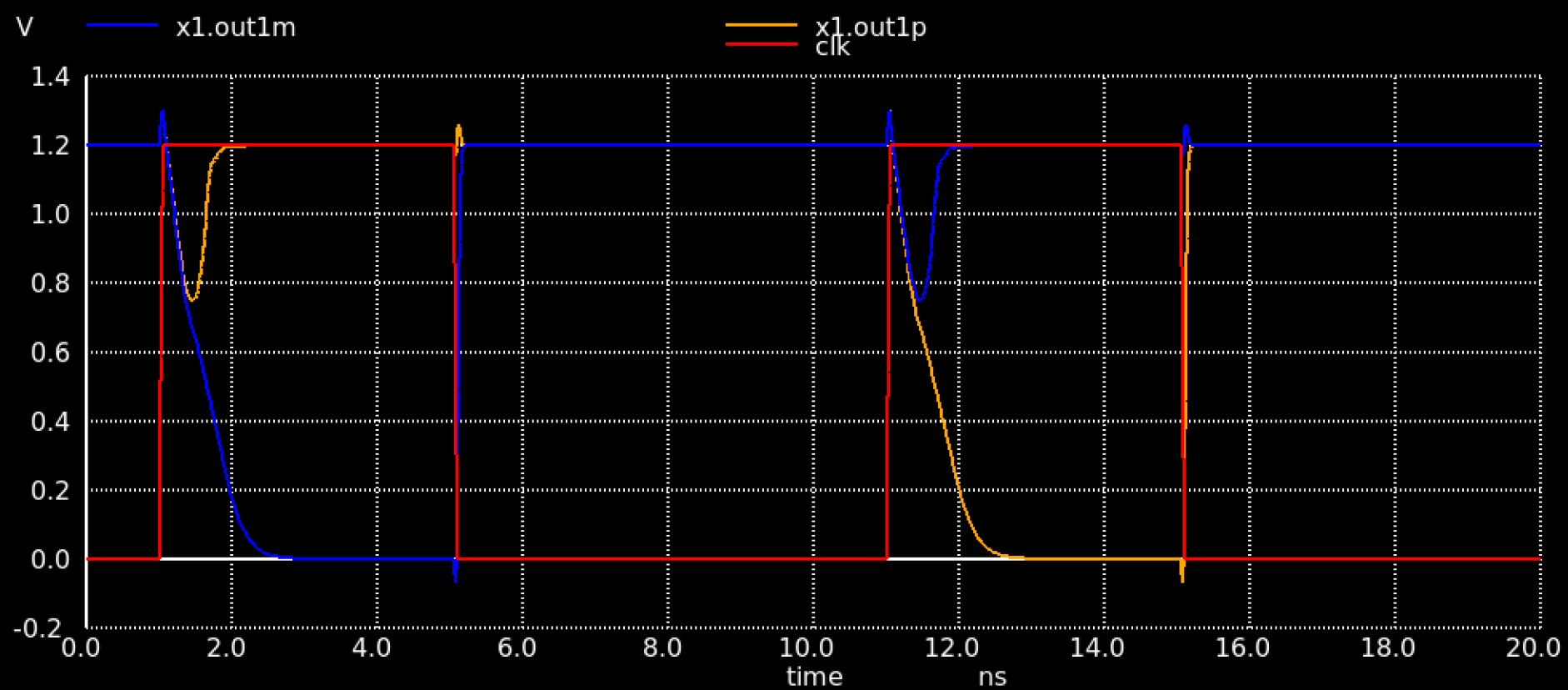


XSCHEM

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/foss/designs/tb_comp.sch

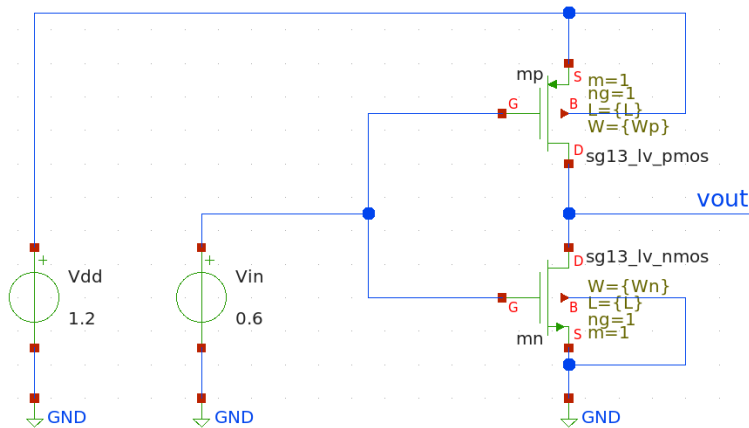
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Next Steps

- Build integrator with inverter
 - Make sure circuit is practical (using VMID instead of GND, etc.)
 - Use reasonably large L for good initial gain
- Verify operation and see how much “effective gain” we can achieve
 - Compare response to idealized circuit without gain enhancement. Adjust VCVS gain until responses are equal → effective gain
 - Note that the improvement may be somewhat less than expected due to the inverter input capacitance
 - See Chae’s paper for details

Inverter Gain in Our Technology



XSCHEM

Boris Murmann

/foss/designs/tb_inv_gain.sch

COMMANDS

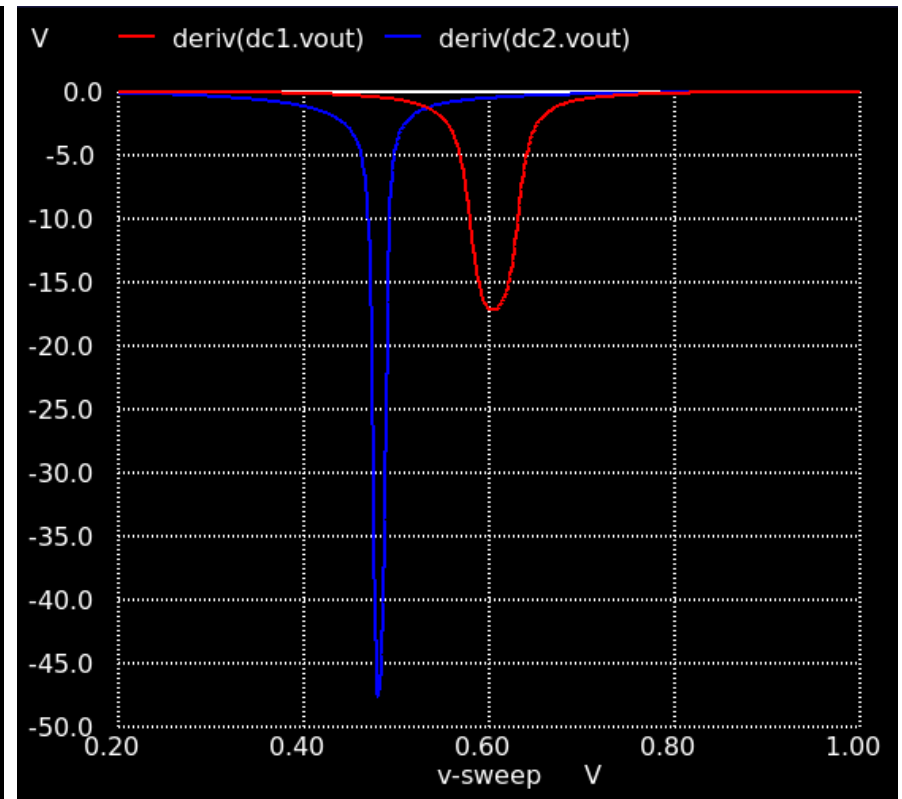
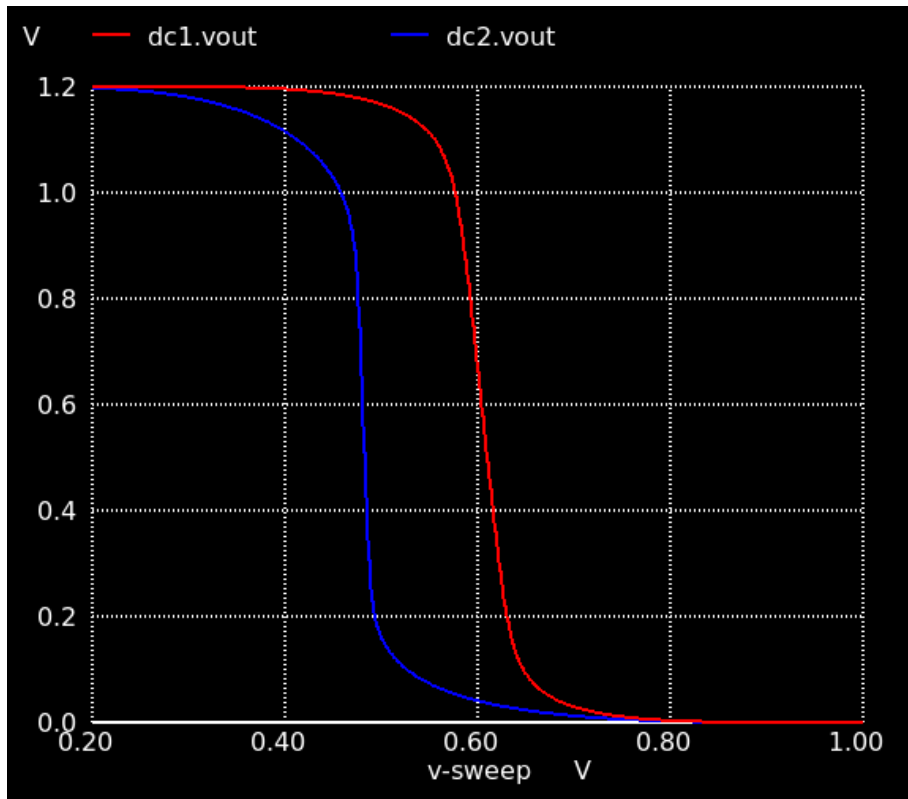
```
.param temp=27
.param Wn=4u Wp={2*Wn} L=0.13u

.control
dc Vin 0.2 1 1m
alterparam L=1.5u
reset
dc Vin 0.2 1 1m
plot dc1.vout dc2.vout
plot deriv(dc1.vout) deriv(dc2.vout)
.endc
```

MODEL

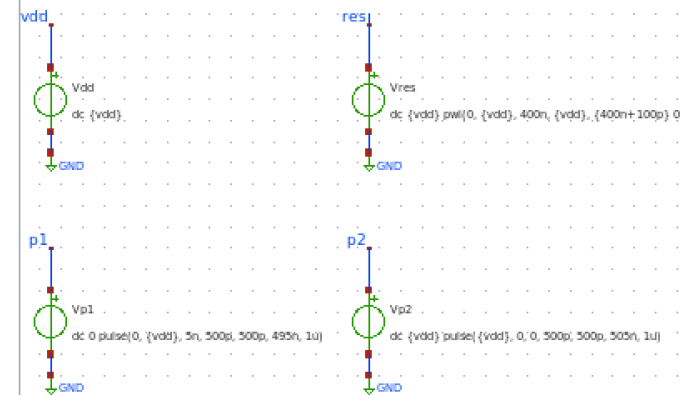
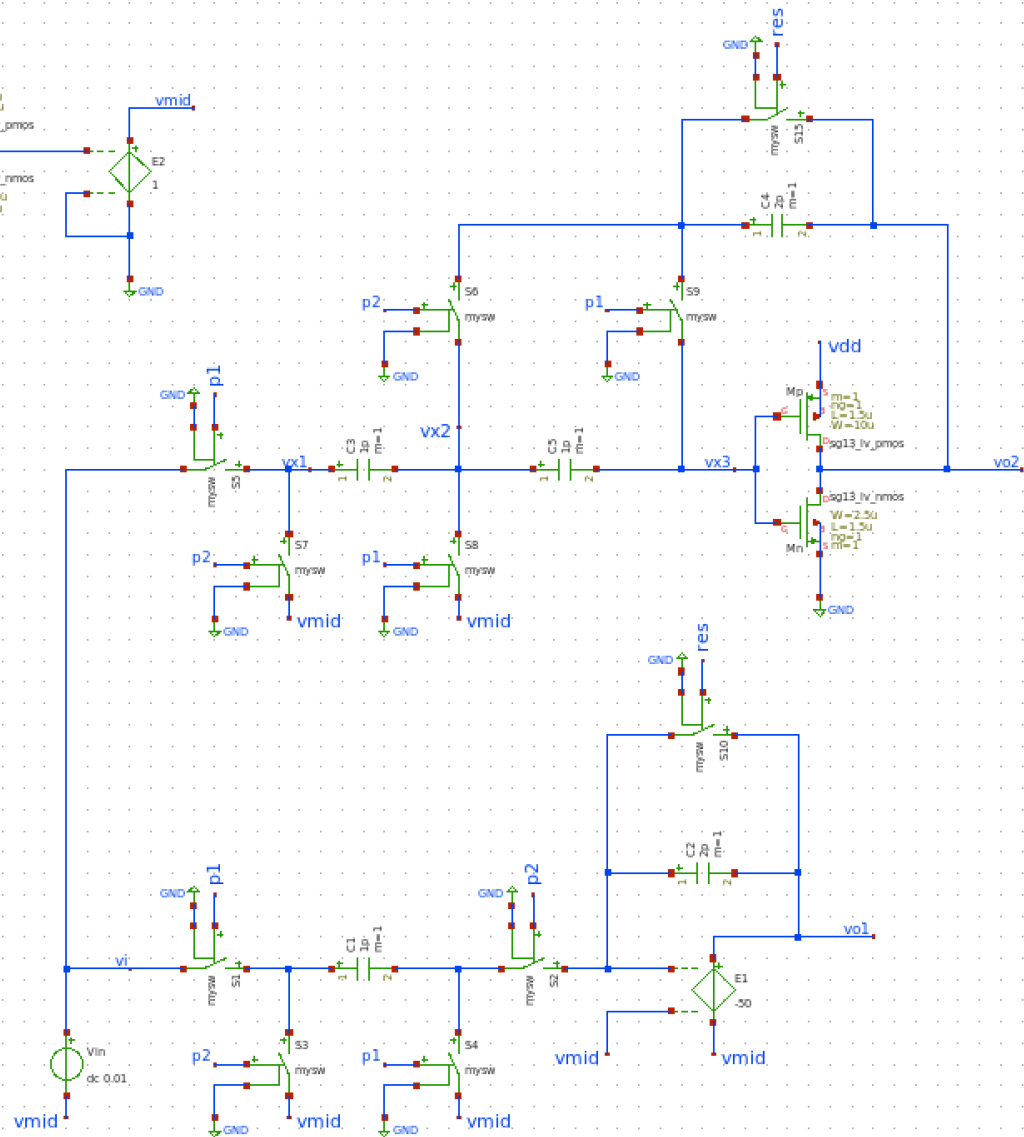
```
.lib $::SG13G2_MODELS/cornerMOSlv.lib mos_tt
```

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Use channel lengths of at least 1.5 μm to get gain close to 50

Inverter-Based Integrator

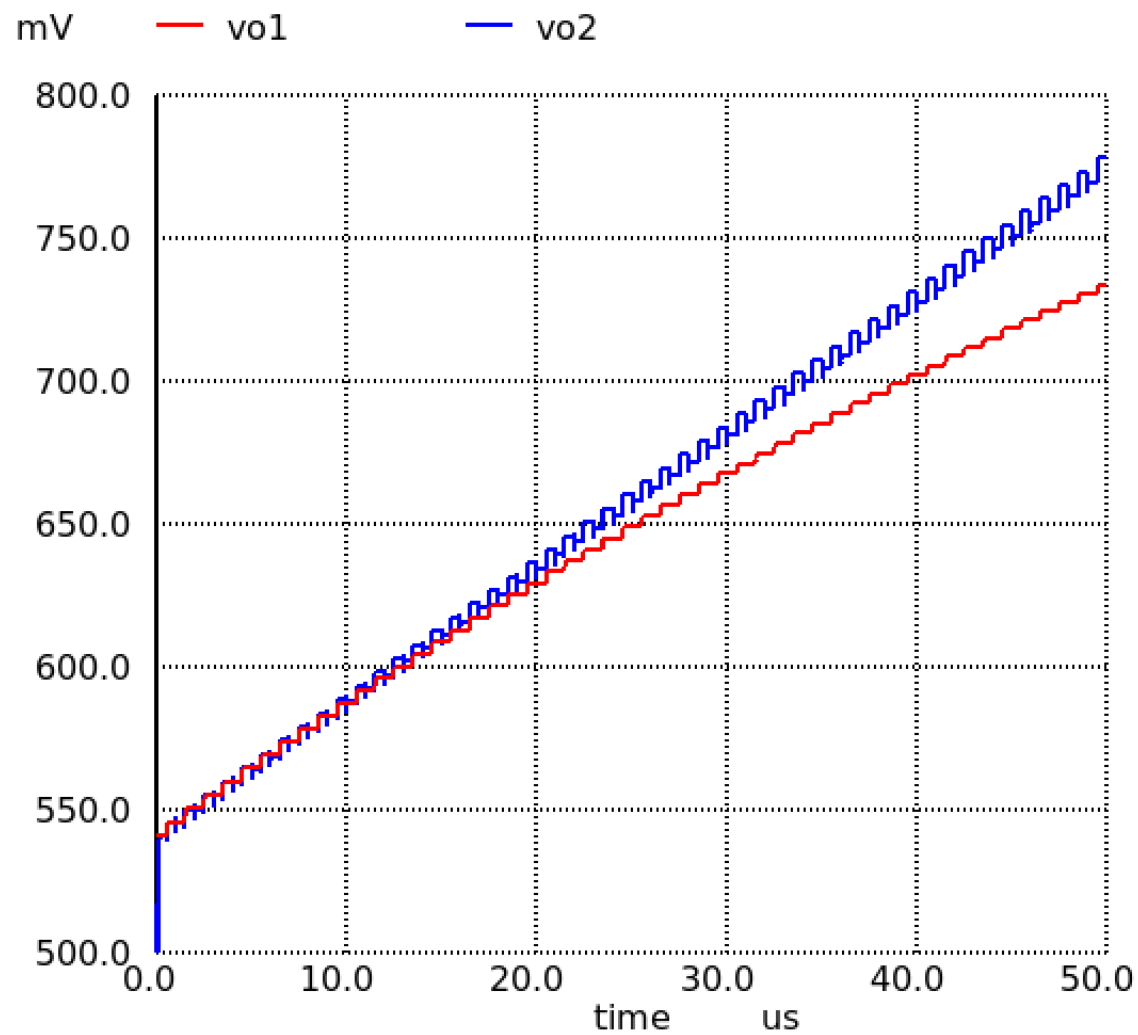


NGSPICE

```
.param temp=27 vdd=1.2
.model msw SW vt={vdd/2} ron=10k roff=10gig
.control
save all
tran 1n 50u
plot vol vo2
.endc
```

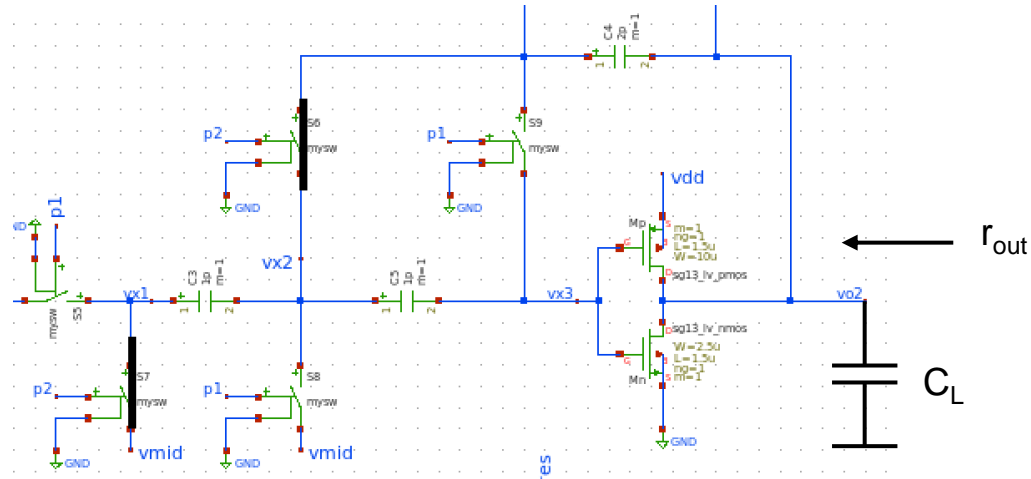
MODEL

```
lib $::SG13G2 MODELS/cornerMOSlv.lib mos tt
```

How Large Should the Inverter Be?

Circuit during p2:



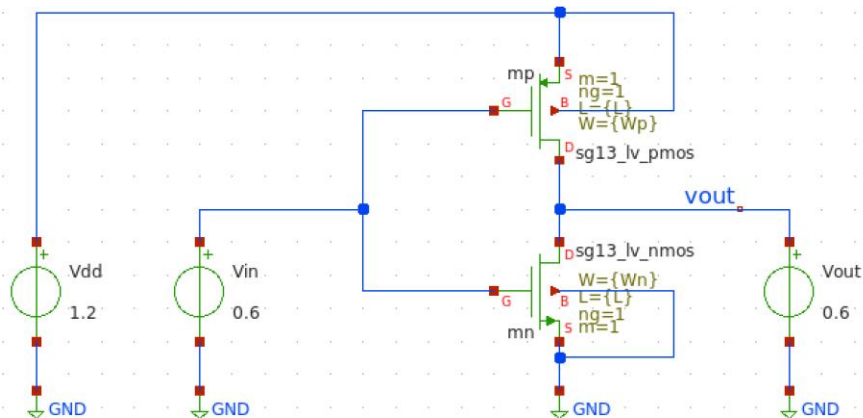
$$r_{out} \approx \frac{1}{\beta(g_{mn} + g_{mp})}$$

$$\beta \approx \frac{C_{int}}{C_{int} + C_s} = \frac{2}{2 + 1} = \frac{2}{3}$$

Need to fit several $\tau = r_{out}C_L$ into half clock period

$$N\tau < \frac{T_s}{2}$$

Measure $g_{mn}+g_{mp}$



COMMANDS

```
.param temp=27
.param Wn=2.5u Wp={4*Wn} L=0.13u

.control
dc Vin 0.2 1 1m
alterparam L=1.5u
reset
dc Vin 0.2 1 1m
set color0 = white
*plot dc1.vout dc2.vout
*plot deriv(dc1.vout) deriv(dc2.vout)
plot i(Vout)
plot deriv(i(Vout))
.endc
```

MODEL

```
.lib $::SG13G2 MODELS/cornerMOSlv.lib mos tt
```



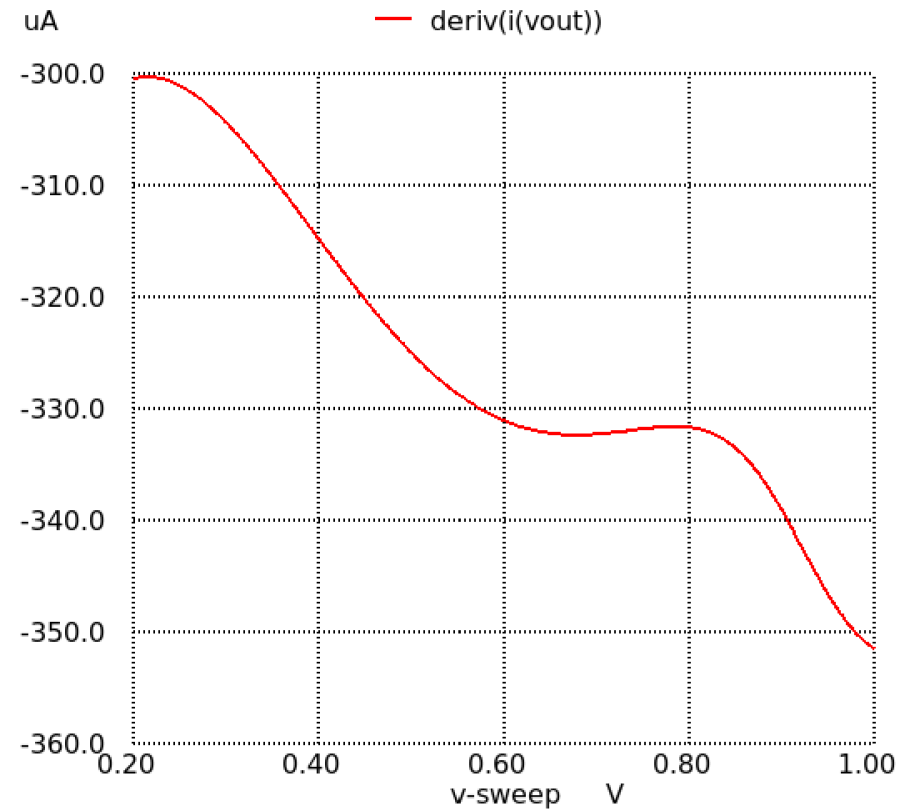
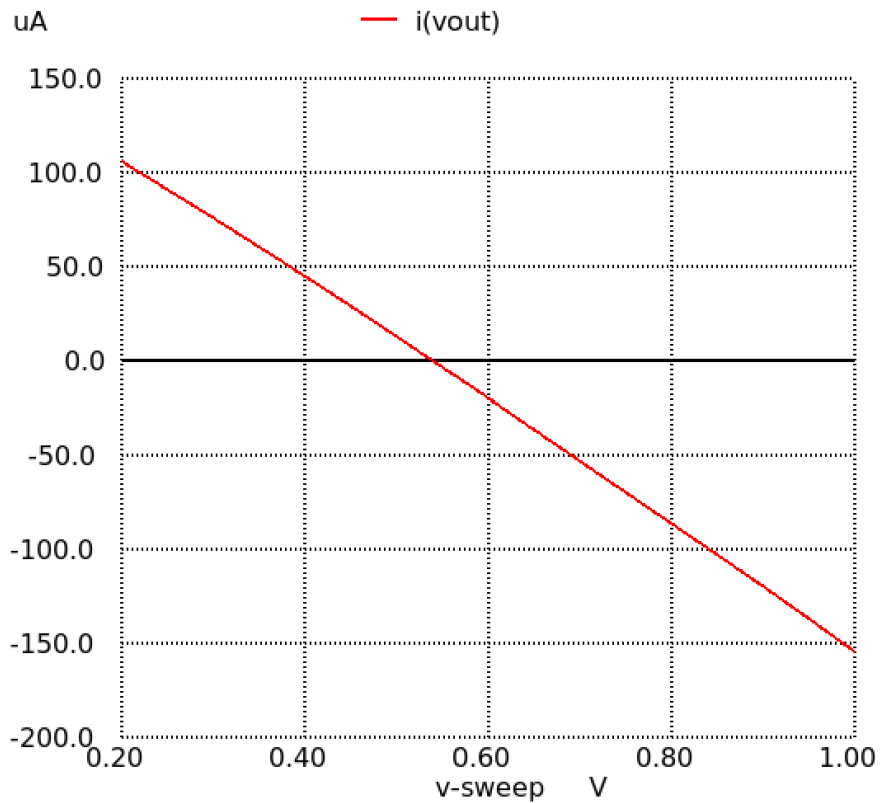
Boris Murmann

```
/foss/designs/tb_inv_gain.sch
```

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Result

$$g_{mn} + g_{mp} \sim 300 \text{ uS}$$



Sizing Example

- The example design by Chae is clocked at 48 MHz
- One half clock cycle is 10.4 ns
- Allow settling for 7 time constants $\rightarrow \tau = 10.4 \text{ ns}/7 = 1.5 \text{ ns}$
- If $C_L = 1 \text{ pF}$, we need $r_{\text{out}} < 1.5 \text{ ns}/1 \text{ pF} = 1.5 \text{ k}\Omega$
- $g_{\text{mn}} + g_{\text{mp}} > 1/1.5 \text{ k}\Omega / \beta = 1 \text{ mS}$

- The transconductance of the simulated inverter is about 0.33 mS
- We need to make the inverter about three times bigger
 - $N = 7.5/1.5$
 - $P = 30/1.5$

- We'll need to revisit this calculation once we know what C_L should be!